

**SURMOUNT™ PIN Diodes**  
**MA4SPS421, MA4SPS422**

**MA4SPS420 Series**  
**V2**

**Features**

- Surface Mount 100 µm I-Region Length Device
- No Wirebonds Required
- Rugged Silicon-Glass Construction
- Silicon Nitride Passivation
- Polymer Scratch Protection
- Low Parasitic Capacitance and Inductance
- Higher Average and Peak Power Handling

**Description and Applications**

This device is a Silicon-Glass PIN diode chip fabricated with M/A-COM's patented HMIC™ process. This device features two silicon pedestals embedded in a low loss, low dispersion glass. The diode is formed on the top of one pedestal and connections to the backside of the device are facilitated by making the pedestal sidewalls electrically conductive. Selective backside metallization is applied producing a surface mount device. This Vertical Topology provides for Exceptional Heat Transfer. The topside is fully encapsulated with silicon nitride and has an additional polymer layer for scratch and impact protection. These protective coatings prevent damage to the junction and the anode air-bridge during handling and assembly.

These packageless devices are suitable for usage in Moderate Incident Power ( 10 W C.W. ) or Higher Incident Peak Power ( 500 W ) Series, Shunt, or Series-Shunt Switches. Smaller Parasitic Inductance, 0.1to 0.2 nH, and Excellent RC Constant ( 0.45 pS ), make the devices ideal for Higher Frequency Switch Elements compared to their Plastic Device Counterparts.

**Dimensions**

Dim	Inches		Millimeters	
	Min.	Max.	Min.	Max.
A	0.040	0.042	1.025	1.075
B	0.021	0.023	0.525	0.575
C	0.004	0.008	0.102	0.203
D	0.013	0.015	0.325	0.375
E	0.011	0.013	0.275	0.325
F	0.013	0.015	0.325	0.375
G	0.019	0.021	0.475	0.525

**Absolute Maximum Ratings<sup>1</sup>**

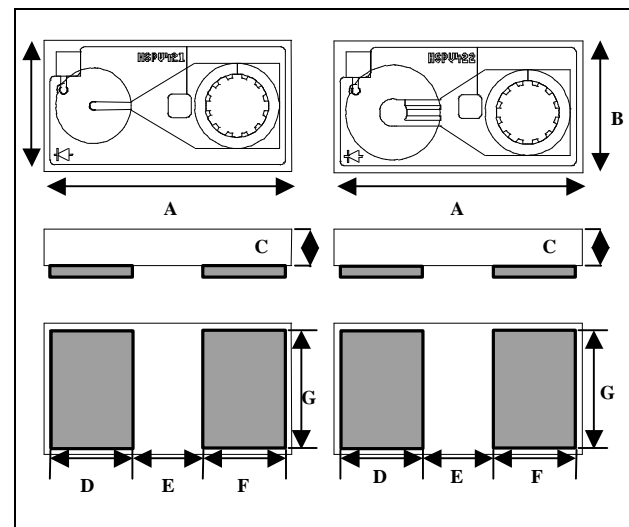
@ TA = +25 °C (unless otherwise specified)

Parameter	Absolute Maximum
Forward Current	250 mA
Reverse Voltage	1-200 V I
Operating Temperature	-55 °C to +125 °C
Storage Temperature	-55 °C to +150 °C
Junction Temperature	+175 °C
Dissipated Power (RF & DC)	1.8 W
Mounting Temperature	+235 °C for 10 seconds

1. Operation of this device above any one of these parameters may cause permanent damage.

**Case Style ODS-1294**  
**(MA4SPS421)**

**Case Style ODS-1295**  
**(MA4SPS422)**



**Bottom Side Contacts are Circuit Side**

1. Backside metal: 0.1 microns thick.
2. Shaded Areas Indicate Backside Ohmic Gold Contacts.
3. Both Devices have Same Outline Dimensions ( A to G ).

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**Electrical Specifications @ + 25 °C**

Parameter	Symbol	Conditions	Units	Min.	Typ.	Max.	Min.	Typ.	Max
				MA4SPS421			MA4SPS422		
Capacitance	C <sub>T</sub>	0 V, 1 MHz <sup>1</sup>	pF		0.130	0.175		0.340	0.500
Capacitance	C <sub>T</sub>	0 V, 1 GHz <sup>1,3</sup>	pF		.08			0.14	
Capacitance	C <sub>T</sub>	-40 Volts, 1 MHz <sup>1</sup>	pF		0.090	0.125		0.180	0.300
Capacitance	C <sub>T</sub>	-40 Volts, 1 GHz <sup>1,3</sup>	pF		.07			0.13	
Resistance	R <sub>S</sub>	+10 mA, 1 GHz <sup>2,3</sup>	Ω		6.2			3.1	
Forward Voltage	V <sub>F</sub>	+10 mA	V		0.900	0.950		0.840	0.900
Reverse Leakage Current	I <sub>R</sub>	I -200 V I	μA			I -10 I			I -10 I
Input Third Order Intercept Point	IIP3	F 1 = 1000 MHz F 2 = 1010 MHz Input Power = +10 dBm I bias = +10 mA	dBm		+50			+50	
C.W. Thermal Resistance	R <sub>θJL</sub>	I <sub>H</sub> = 0.5 A, I <sub>L</sub> = 10 mA	°C/W		80			70	
Minority Carrier Lifetime	T <sub>L</sub>	+10 mA / -6 mA (50% - 90% V)	μs		5			10	

1. Total capacitance, C<sub>T</sub>, is equivalent to the sum of Junction Capacitance, C<sub>J</sub>, and Parasitic Capacitance, C<sub>par</sub>.
2. Series resistance R<sub>S</sub> is equivalent to the total diode resistance : R<sub>S</sub> = R<sub>J</sub> ( Junction Resistance) + R<sub>C</sub> ( Ohmic Resistance)
3. R<sub>S</sub> and C<sub>T</sub> are measured on an HP4291A Impedance Analyzer with die mounted in an ODS-186 package with Sn 60 / Pb 40 solder.
4. Steady-state R<sub>θJL</sub> measured with die mounted in an ODS-186 package with Sn 60 / Pb 40 solder.

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**V2****Handling**

All semiconductor chips should be handled with care to avoid damage or contamination from perspiration and skin oils. The use of plastic tipped tweezers or vacuum pickups is strongly recommended for individual components. Bulk handling should insure that abrasion and mechanical shock are minimized.

**Bonding**

Attachment to a circuit board is made simple through the use of surface mount technology. Mounting pads are conveniently located on the bottom surface of these devices and are removed from the active junction locations. These devices are well suited for solder attachment onto hard and soft substrates. The use of 80 Au / 20 Sn or Sn 60 / Pb 40 solder is recommended. Conductive silver epoxy for die attachment may also be used for lower incident power (<1 W average incident power) applications.

When soldering these devices to a hard substrate, hot gas die bonding is preferred. We re-commend utilizing a vacuum tip and force of 60 to 100 grams applied normal to the top surface of the device. When soldering to soft substrates, it is recommended to use a lead-tin interface at the circuit board mounting pads. Position the die so that its mounting pads are aligned with the circuit board mounting pads and reflow the solder by heating the circuit trace near the mounting pad while applying 60 to 100 grams of force perpendicular to the top surface of the die. The solder joint must Not be made one at a time, creating un-equal heat flow and thermal stress. Solder reflow should Not be performed by causing heat to flow through the top surface of the die. Since the HMIC glass is transparent, the edges of the mounting pads closest to each other can be visually inspected through the die after attach is completed.

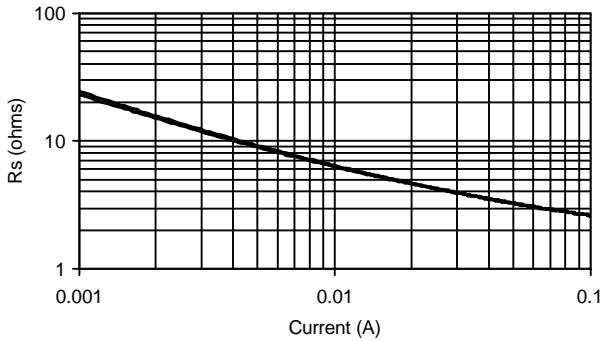
A typical profile for a Sn 60/ Pb 40 Soldering process is provided in [Application Note, " M538 "](#) , [" Surface Mounting Instructions "](#) on the MA-COM website [www.macom.com](http://www.macom.com).

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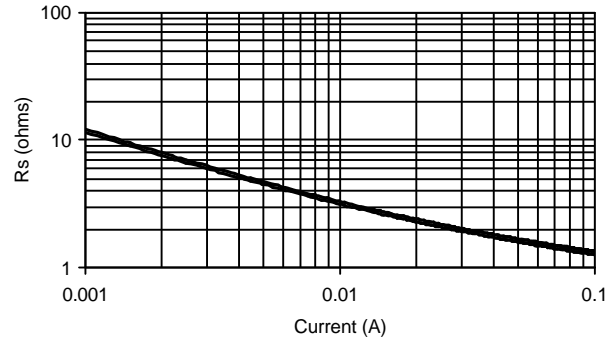
**MA4SPS420 Series**  
**V2**

**MA4SPS420 Typical Performance Curves @ +25 °C**

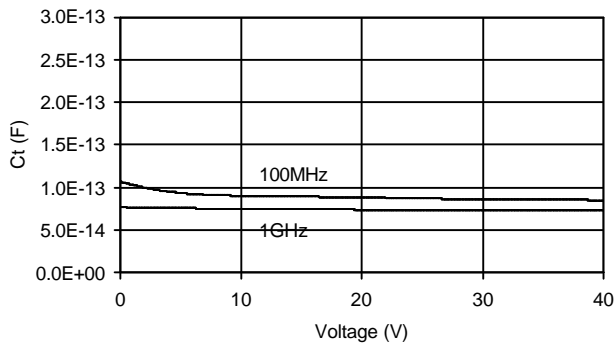
Rs vs. Current (@ 100MHz & 1GHz)  
MA4SPS421



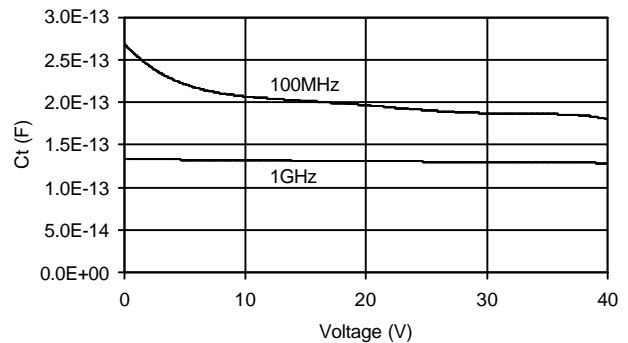
Rs vs. Current (@ 100MHz & 1GHz)  
MA4SPS422



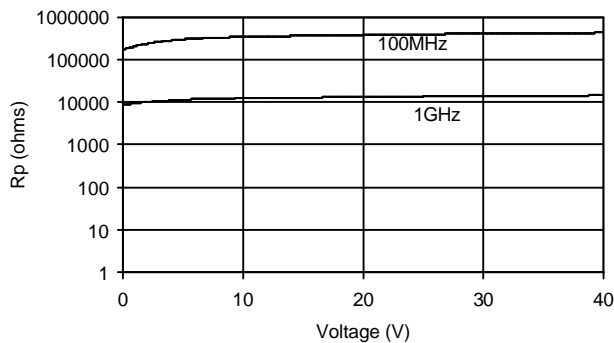
Ct vs Voltage (@ 100MHz & 1GHz)  
MA4SPS421



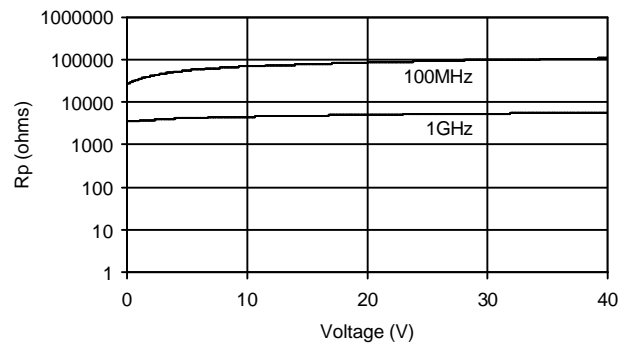
Ct vs Voltage (@ 100MHz & 1GHz)  
MA4SPS422



Rp vs Voltage (@ 100MHz & 1GHz)  
MA4SPS421



Rp vs Voltage (@ 100MHz & 1GHz)  
MA4SPS422

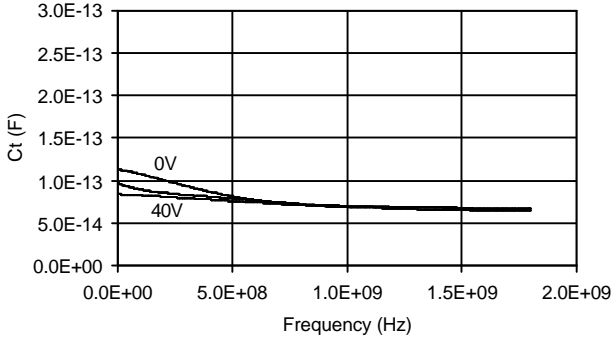


**SURMOUNT™ PIN Diodes  
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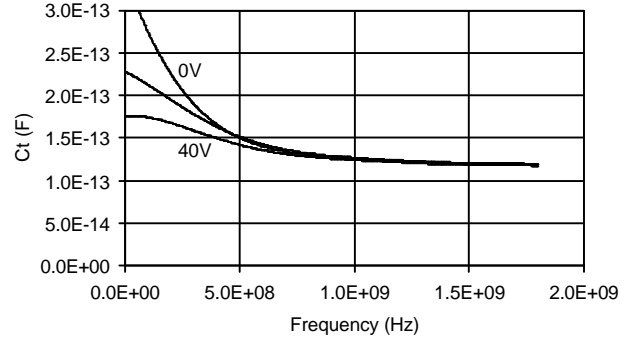
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**MA4SPS420 Typical Performance Curves @ +25 °C**

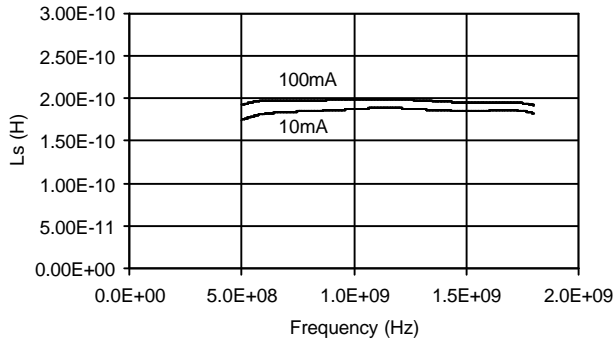
Ct vs Frequency (@ 0, 5 & 40V)  
MA4SPS421



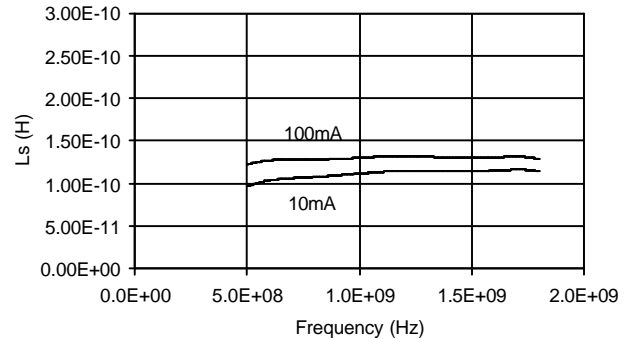
Ct vs Frequency (@ 0, 5 & 40V)  
MA4SPS422



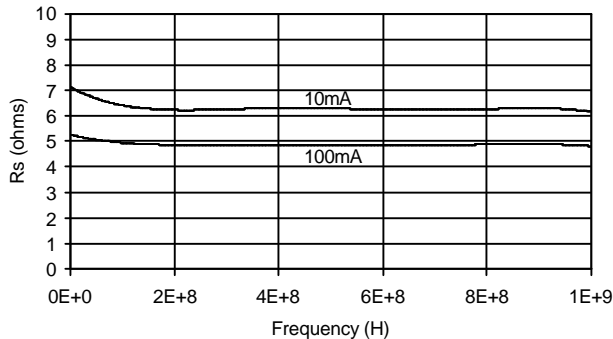
Ls vs Frequency (@ 10mA & 100mA)  
MA4SPS421



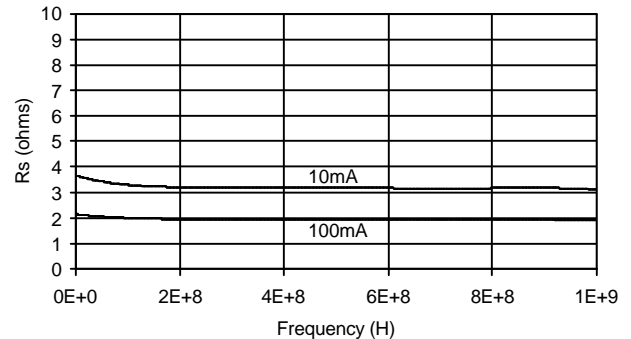
Ls vs Frequency (@ 10mA & 100mA)  
MA4SPS422



Rs vs Frequency (@ 10mA & 100mA)  
MA4SPS421



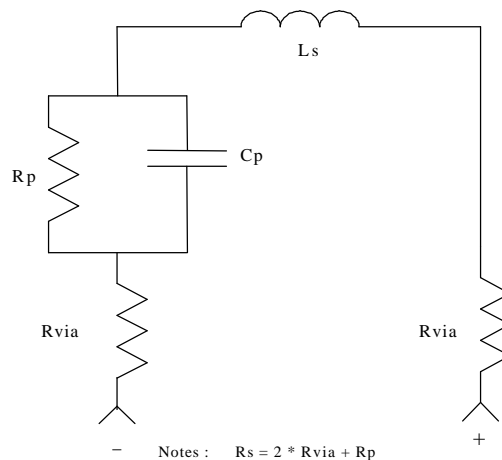
Rs vs Frequency (@ 10mA & 100mA)  
MA4SPS422



**MA4SPS421 SPICE Model**

PinDiodeModel	wBv=260 V
NLPINM1	wPmax=1.6 W
Is=1.0E-14 A	Ffe=1.0
Vi=0.0 V	
Un=900 cm <sup>2</sup> /V-sec	
Wi=100 um	
Rr=11 K Ohm	
Cmin=0.06 pF	
Tau= 5 usec	
Rs=0.1 Ohm	
Cj0=0.07 pF	
Vj=0.7 V	
M=0.5	
Fc=0.5	
Imax=3.1 E+8 A/m <sup>2</sup>	
Kf=0.0	
Af=1.0	

**MA4SPS421 Schematic**



**MA4SPS422 SPICE Model**

PinDiodeModel            wBv=340 V  
 NLPINM1                wPmax=1.8 W  
 Is=1.0E-14 A            Ffe=1.0  
 Vi=0.0 V  
 Un=900 cm<sup>2</sup>/V-sec  
 Wi=100 um  
 Rr=9 K Ohm  
 Cmin=0.12 pF  
 Tau= 10 usec  
 Rs=0.1 Ohm  
 Cj0=0.13 pF  
 Vj=0.7 V  
 M=0.5  
 Fc=0.5  
 Imax=7.8 E+7 A/m<sup>2</sup>  
 Kf=0.0  
 Af=1.0

**MA4SPS422 Schematic**

